

L Number	r Hits	Search Text	DB	Time stamp
-	1192	@ad<=20010104 and 'heating substrate' and	USPAT; US-PGPUB;	2002/10/24 14:28
		'amorphous silicon'	EPO; JPO;	1
			DERWENT;	1
			IBM TDB	
_	943	((438/486) or (438/482)).CCLS.	USPĀT;	2002/10/03 13:05
	-		US-PGPUB;	
ı			EPO; JPO;	
			DERWENT;	
	71	(((438/486) or (438/482)).CCLS.) and	IBM_TDB USPAT;	2002/10/03 13:00
-	, 1	@ad<=20010104 and 'heating substrate' and	US-PGPUB;	2002, 20, 00 10.00
		'amorphous silicon'	EPO; JPO;	
		•	DERWENT;	
			IBM_TDB	
-	2	(@ad<=20010104 and 'heating substrate' and	USPAT;	2002/10/03 13:18
		'amorphous silicon') and @ad<=20010104	US-PGPUB;	
		and 'heating substrate' and 'amorphous	EPO; JPO; DERWENT;	
		silicon' and MILC	IBM TDB	
	2	(((438/486) or (438/482)).CCLS.) and MILC	USPAT;	2002/10/03 13:36
		and 'low temperature'	US-PGPUB;	
	{	•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
, -	2		USPAT;	2002/10/03 13:06
		'amorphous silicon') and MILC and 'low	US-PGPUB;	
		temperature'	EPO; JPO; DERWENT;	
	-		IBM TDB	
_	0	@ad<=20010104 and 'amorphous silicon' with	USPAT;	2002/10/03 13:11
		'metal layer' and 'heating' with 'while	US-PGPUB;	
		depositing'	EPO; JPO;	
			DERWENT;	
_		0 1 00010104	IBM_TDB	! - 2002/10/02 12:11
	181	<pre>@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating'</pre>	USPAT; US-PGPUB;	2002/10/03 13:11
		metal layer and heating	EPO; JPO;	i
			DERWENT;	
)		IBM TDB	
-	109		USPAT;	2002/10/03 13:11
		with 'metal layer' and 'heating') and	US-PGPUB;	
		'depositing'	EPO; JPO;	
	ļ		DERWENT;	
	1.4	Rade-20010104 and lamorphous silicon! with	IBM_TDB USPAT;	2002/10/03 13:11
_	14	<pre>@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating' with</pre>	US-PGPUB;	2002, 10,00 10.11
		'depositing'	EPO; JPO;	I
			DERWENT;	t
			IBM_TDB	
-	2		USPAT;	2002/10/24 13:10
	-	'amorphous silicon') and @ad<=20010104	US-PGPUB;	
		and 'amorphous silicon' and MILC	EPO; JPO; DERWENT;	
			IBM TDB	i
_	303	(((438/486) or (438/482)).CCLS.) and 'low	USPAT;	2002/10/03 13:37
		temperature'	US-PGPUB;	1
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/10/02 13 35
-	52	(((438/486) or (438/482)).CCLS.) and 'low	USPAT;	2002/10/03 13:37
		temperature' and 'heating substrate'	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	0	@ad<=20010104 and heating adj1 substrate	USPĀT;	2002/10/24 13:51
		with depositing same metal and MILC	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	

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C:\APPS\east\workspaces\Thin Film Transistor 438_149\10038990 low temp crys a_si 438_486.wsp



1' -	_	58	@ad<=20010104 and MILC	USPAT; US-PGPUB;	7 2002/10/24 13:18
				EPO; JPO; DERWENT; IBM TDB	
	-	0	@ad<=20010104 and heating adjl substrate adjl while same 'depositing metal'	USPĀT; US-PGPUB;	2002/10/24 13:54
				EPO; JPO; DERWENT; IBM TDB	
-	-	0	@ad<=20010104 and heat adj1 substrate adj1 while same 'depositing metal'	USPĀT; US-PGPUB;	2002/10/24 13:54
				EPO; JPO; DERWENT; IBM TDB	
-	-	3	@ad<=20010104 and heat adj1 substrate same 'depositing metal'	USPAT; US-PGPUB;	2002/10/24 13:56
		-		EPO; JPO; DERWENT; IBM TDB	1
_	- '	74	@ad<=20010104 and heating adjl substrate same 'depositing metal'	USPAT; US-PGPUB;	2002/10/24 14:15
i				EPO; JPO; DERWENT; IBM TDB	
	-	15	@ad<=20010104 and 'hot metallization'	USPĀT; US-PGPUB;	2002/10/24 14:16
				EPO; JPO; DERWENT; IBM TDB	
	-	191	@ad<=20010104 and 'amorphous silicon' same 'heating substrate'	USPAT; US-PGPUB;	2002/10/24 15:55
ļ				EPO; JPO; DERWENT;	
	-	12	@ad<=20010104 and 'amorphous silicon' same 'heating substrate' same 'metal'	IBM_TDB USPAT; US-PGPUB;	2002/10/24 15:40
	i		-	EPO; JPO; DERWENT;	1
	_	- 3778	((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.	IBM_TDB USPAT; US-PGPUB;	2002/10/24 15:42
	ĺ			EPO; JPO; DERWENT;	
	-	54	(((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.) and	IBM_TDB USPAT; US-PGPUB;	2002/10/24 15:56
			@ad<=20010104 and 'heating substrate'	EPO; JPO; DERWENT;	
l				IBM TDB	<u> </u>